DATA SHEET

MAC223 series
Triacs

Product specification July 2001

Philips Semiconductors

PHILIPS

Triacs | MAC223 series

GENERAL DESCRIPTION

Passivated triacs in a plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

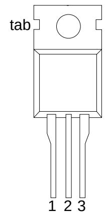
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX	MAX.	UNIT
	MAC223	A6	A8	
V_{DRM}	Repetitive peak off-state voltages	400	600	V
$I_{T(RMS)}$	RMS on-state current	25	25	A
I_{TSM}	Non-repetitive peak on-state current	230	230	A

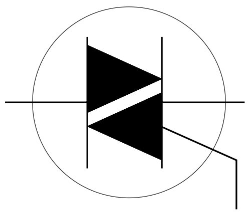
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
		MAC223		A6	A8	
V_{DRM}	Repetitive peak off-state voltages		-	400[1]	600[1]	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 91$ ˚C	-	25		A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25$ ˚C prior to surge				
		t = 20 ms	-	190		A
		t = 16.7 ms	-	230		A
I^2t	I^2t for fusing	t = 10 ms	-	180		A^2s
dI_T/dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 30$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/µs				
		T2+ G+	-	50		A/µs
		T2+ G-	-	50		A/µs
		T2- G-	-	50		A/µs
		T2- G+	-	10		A/µs
I_{GM}	Peak gate current		-	2		A
V_{GM}	Peak gate voltage		-	5		V
P_{GM}	Peak gate power		-	5		W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5		W
T_{stg}	Storage temperature		-40	150		˚C
T_j	Operating junction temperature		-	125		˚C

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base	full cycle	-	-	1.0	K/W
		half cycle	-	-	1.4	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air	-	60	-	K/W

STATIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	V_D = 12 V; I_T = 0.1 A				
		T2+ G+	-	6	50	mA
		T2+ G-	-	10	50	mA
		T2- G-	-	11	50	mA
		T2- G+	-	23	75	mA
I_L	Latching current	V_D = 12 V; I_{GT} = 0.1 A				
		T2+ G+	-	8	40	mA
		T2+ G-	-	30	60	mA
		T2- G-	-	18	40	mA
		T2- G+	-	15	60	mA
I_H	Holding current	V_D = 12 V; I_{GT} = 0.1 A				
		T2+	-	7	30	mA
		T2-	-	12	30	mA
V_T	On-state voltage	I_T = 30 A	-	1.3	1.55	V
V_{GT}	Gate trigger voltage	V_D = 12 V; I_T = 0.1 A	-	0.7	1.5	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 ˚C	0.25	0.4	-	V
I_D	Off-state leakage current	$V_D = V_{DRM(max)}$; T_j = 125 ˚C	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	V_{DM} = 67% $V_{DRM(max)}$; T_j = 125 ˚C; exponential waveform; gate open circuit	100	300	-	V/µs
dV_{com}/dt	Critical rate of change of commutating voltage	V_{DM} = 400 V; T_j = 95 ˚C; $I_{T(RMS)}$ = 25 A; dI_{com}/dt = 9 A/ms; gate open circuit	-	10	-	V/µs
t_{gt}	Gate controlled turn-on time	I_{TM} = 30 A; $V_D = V_{DRM(max)}$; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	2	-	µs

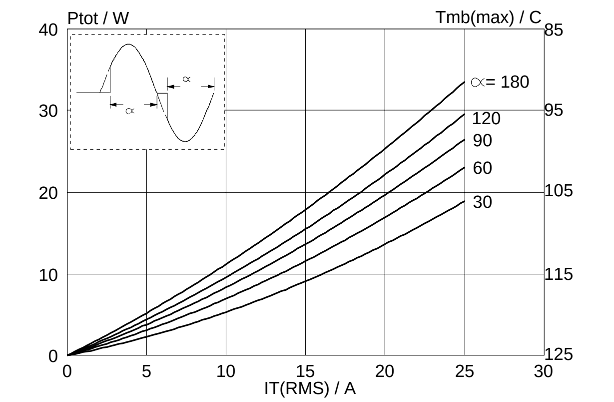


Fig.1. Maximum on-state dissipation, P_{tot}, versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

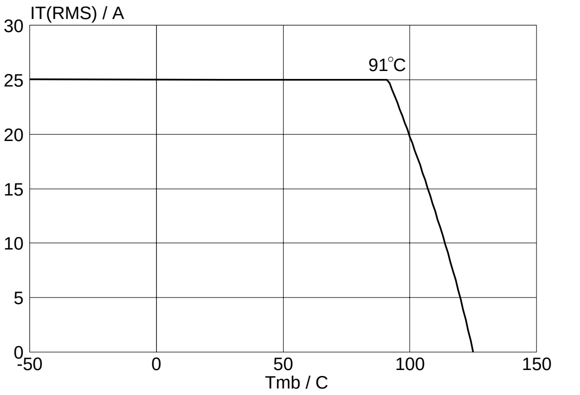


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb}.

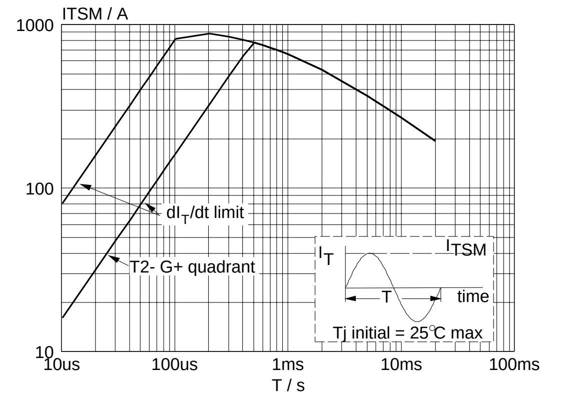


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus pulse width t_p, for sinusoidal currents, $t_p \leq 20ms$.

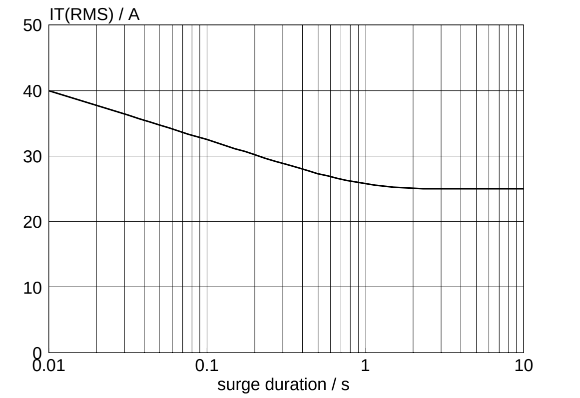


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \leq 91^{\circ}C$.

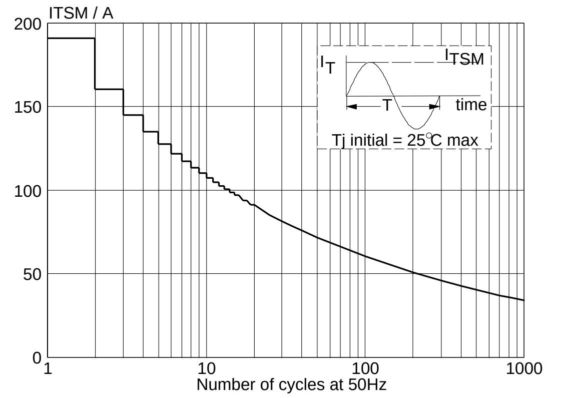


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus number of cycles, for sinusoidal currents, f = 50 Hz.

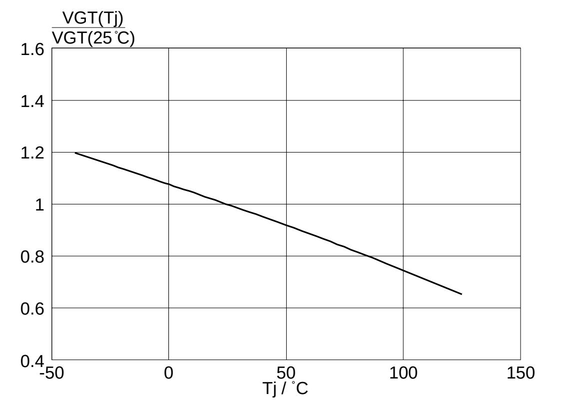


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/ V_{GT}(25^{\circ}C)$, versus junction temperature T_j.

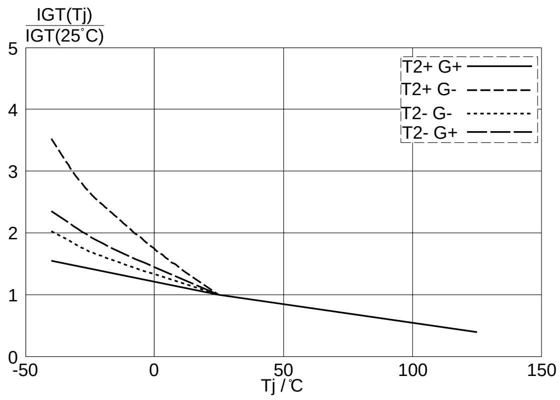


Fig.7. Normalised gate trigger current $I_{GT}(T_j)/\ I_{GT}(25˚C)$, versus junction temperature T_j.

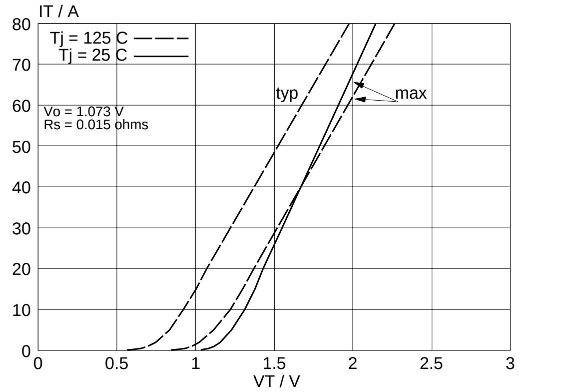


Fig.10. Typical and maximum on-state characteristic.

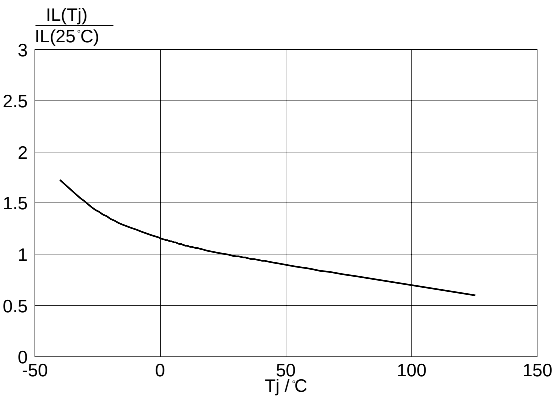


Fig.8. Normalised latching current $I_L(T_j)/\ I_L(25˚C)$, versus junction temperature T_j.

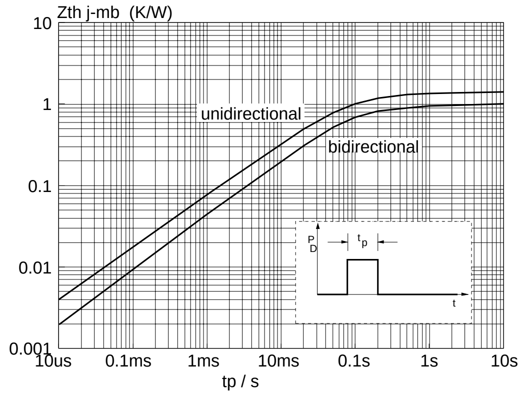


Fig.11. Transient thermal impedance $Z_{th\ j\text{-}mb}$, versus pulse width t_p.

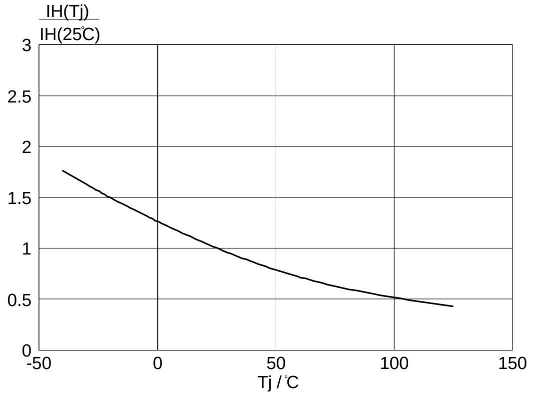


Fig.9. Normalised holding current $I_H(T_j)/\ I_H(25˚C)$, versus junction temperature T_j.

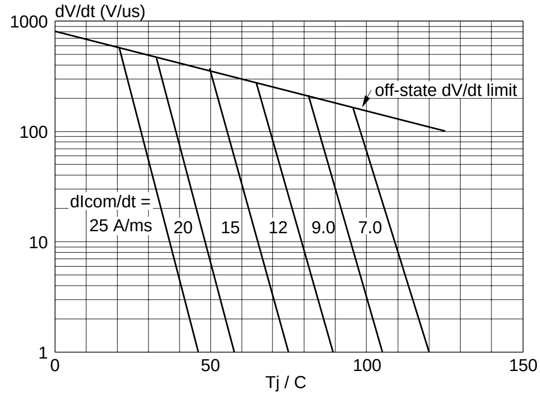


Fig.12. Typical commutation dV/dt versus junction temperature, parameter commutation dI_T/dt. The triac should commutate when the dV/dt is below the value on the appropriate curve for pre-commutation dI_T/dt.

Dimensions in mm

Net Mass: 2 g

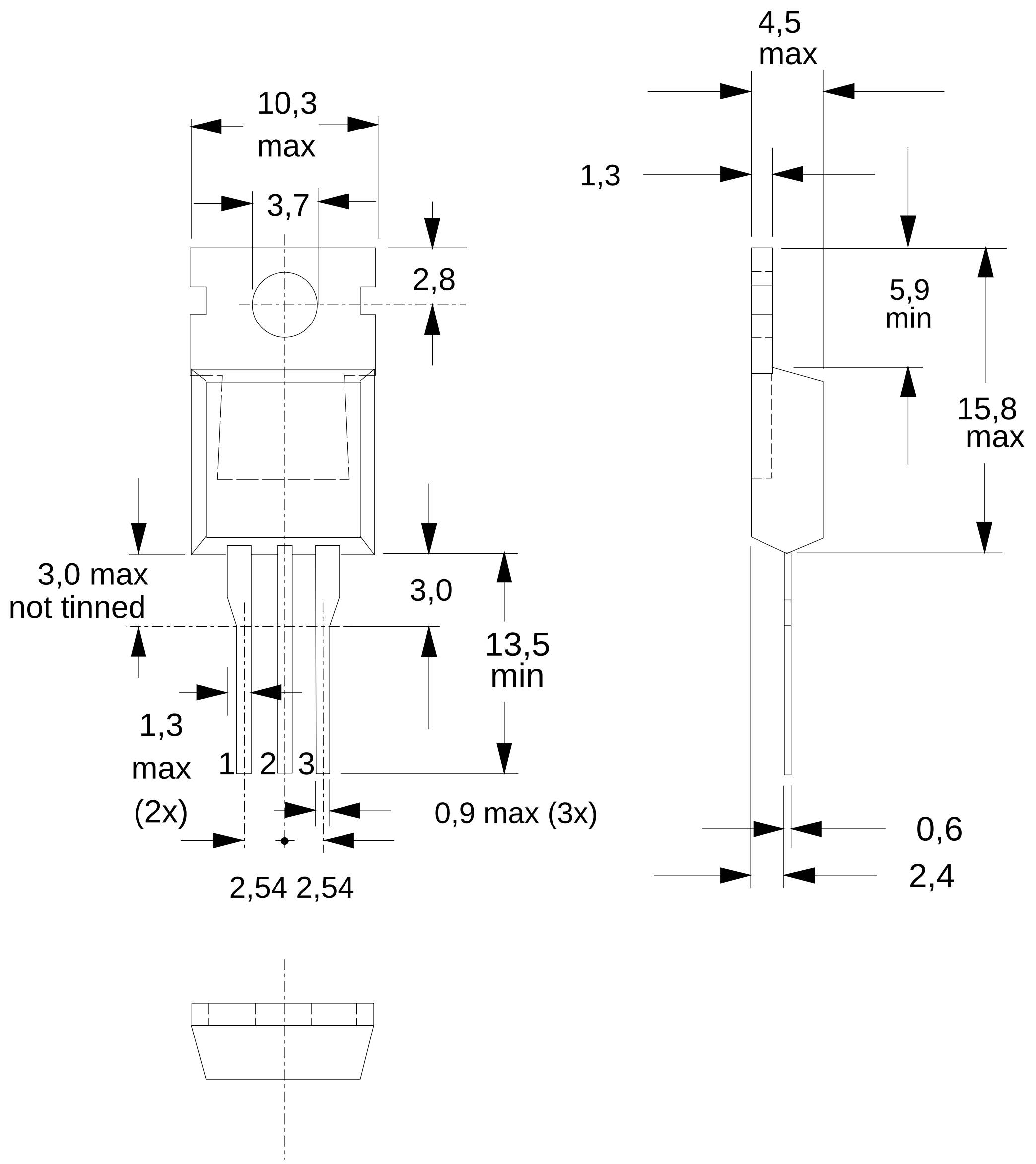


Fig.13. SOT78 (TO220AB). pin 2 connected to mounting base.

Notes
1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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